

DESCRIPTION

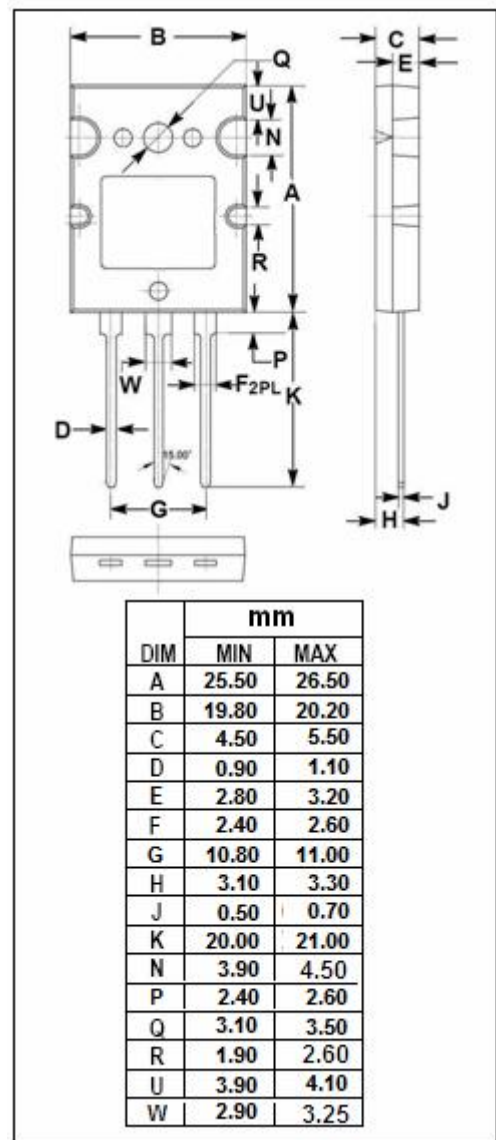
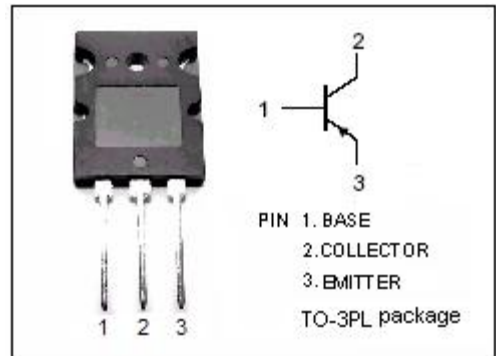
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -250V(\text{Min})$
High DC Current Gain – $hFE = 25 \text{ Min @ } I_C = 8 \text{ Adc}$
- Complement to Type MJL21194

APPLICATIONS

Perforated Emitter technology
high power audio output, disk head positioners
linear applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-16	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	200	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-250			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -8.0\text{A}; I_B = -0.8\text{A}$			-1.4	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -16\text{A}; I_B = -3.2\text{A}$			-4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -8\text{A}; V_{CE} = -5\text{V}$			-2.2	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -200\text{V}; I_E = 0$			-100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-100	μA
h_{FE-1}	DC Current Gain	$I_C = -8\text{A}; V_{CE} = -5\text{V}$	25		75	
h_{FE-2}	DC Current Gain	$I_C = -16\text{A}; V_{CE} = -5\text{V}$	8			
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$			500	pF
f_T	Current-Gain—Bandwidth Product	$I_C = -1\text{A}; V_{CE} = -10\text{V}$	4			MHz
$I_{s/b}$	Second Breakdown Collector Current with Base Forward Biased	$V_{CE} = 50\text{V}, t = 1.0\text{s}$	4			A
		$V_{CE} = 80\text{V}, t = 1.0\text{s}$	2.25			A